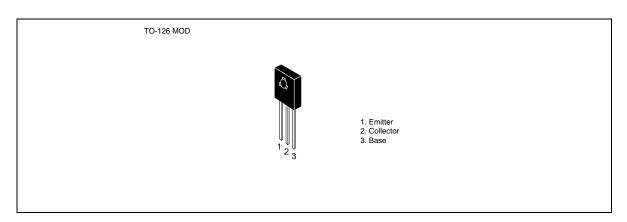
Silicon NPN Epitaxial

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Application

High voltage amplifier

Outline



Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	Ratings	Unit V	
Collector to base voltage	V _{cbo}	120		
Collector to emitter voltage	V _{CEO} 120		V	
Emitter to base voltage	V _{ebo}	5	V	
Collector current	Ι _c	0.2	A	
Collector power dissipation	P _c * ¹	8	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
Note: 1. Value at $T_c = 25^{\circ}C$				

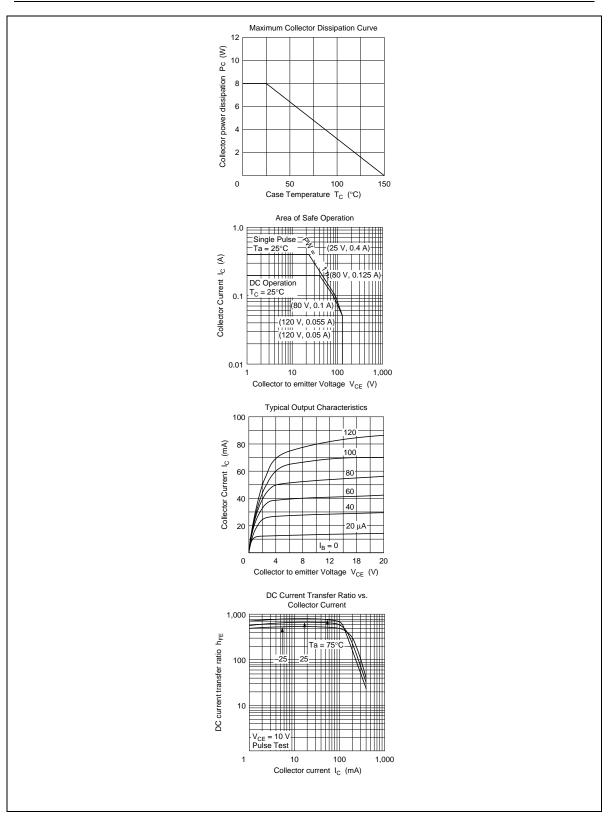
Electrical Characteristics (Ta = 25°C)

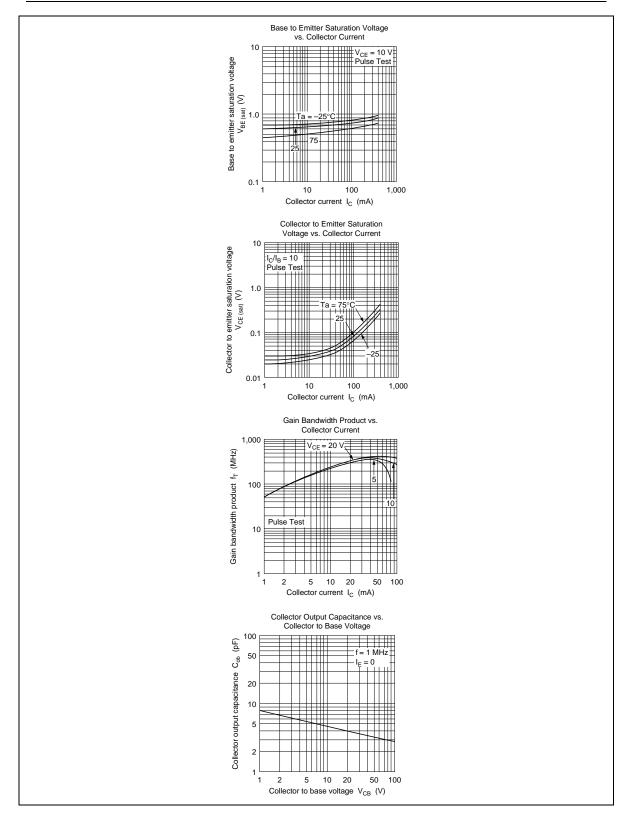
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\scriptscriptstyle (BR)CBO}$	120	_		V	$I_{c} = 10 \ \mu A, I_{e} = 0$
Collector to emitter breakdown voltage	$V_{\scriptscriptstyle (BR)CEO}$	120	—	—	V	$I_{c} = 1 \text{ mA}, R_{BE} = _{-}$
Emitter to base breakdown voltage	$V_{\scriptscriptstyle (BR)EBO}$	5	_	_	V	$I_{\rm e} = 10 \ \mu A, \ I_{\rm c} = 0$
Collector cutoff current	I _{cbo}		—	10	μA	$V_{_{CB}} = 80 \text{ V}, \text{ I}_{_{E}} = 0$
DC current transfer ratio	$h_{\rm FE}^{*1}$	250	_	800		$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 10 \text{ mA}$
Base to emitter voltage	V _{BE}	_	_	1.0	V	_
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.0	V	$I_{c} = 200 \text{ mA}, I_{B} = 20 \text{ mA}$
Gain bandwidth product	f _T	_	350	_	MHz	$V_{ce} = 10 \text{ V}, \text{ I}_{c} = 50 \text{ mA}$
Collector output capacitance	Cob	_	3.5	_	pF	$V_{_{CB}} = 30 \text{ V}, \text{ f} = 1 \text{ MHz}, \text{ I}_{_{E}} = 0$

Note: 1. The 2SC4046 is grouped by h_{FE} as follows.

 Grade
 D
 E

 h_{FE}
 250 to 500
 400 to 800





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